

Silicon PNP Power Transistors

2SB1034

DESCRIPTION

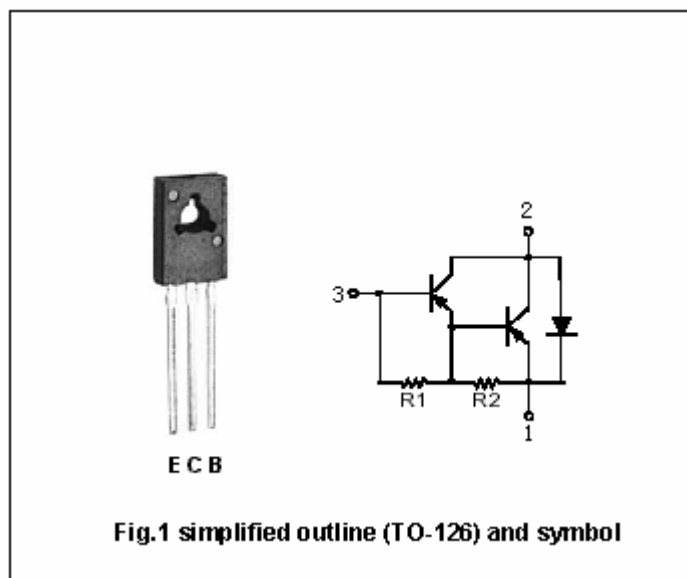
- With TO-126 package
- Low collector saturation voltage
- High DC current gain
- DARLINGTON

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current (DC)		-2	A
I_B	Base current (DC)		-0.5	A
P_C	Total power dissipation	$T_C=25^\circ\text{C}$	15	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10\text{mA}$; $I_B = 0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -1\text{A}$; $I_B = -1\text{mA}$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -1\text{A}$; $I_B = -1\text{mA}$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -80\text{V}$; $I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -8\text{V}$; $I_C = 0$			-4	mA
h_{FE}	DC current gain	$I_C = -1\text{A}$; $V_{CE} = -2\text{V}$	2000			
C_{OB}	Output capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f = 1\text{MHz}$		30		pF
f_T	Transition frequency	$I_C = -0.5\text{A}$; $V_{CE} = -2\text{V}$		50		MHz

Switching times

t_{on}	Turn-on time	$R_L = 30\Omega$ $I_{B1} = I_{B2} = 1\text{mA}$ $V_{CC} = -30\text{V}$		0.4		μs
t_s	Storage time			2.0		μs
t_f	Fall time			0.4		μs

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PACKAGE OUTLINE

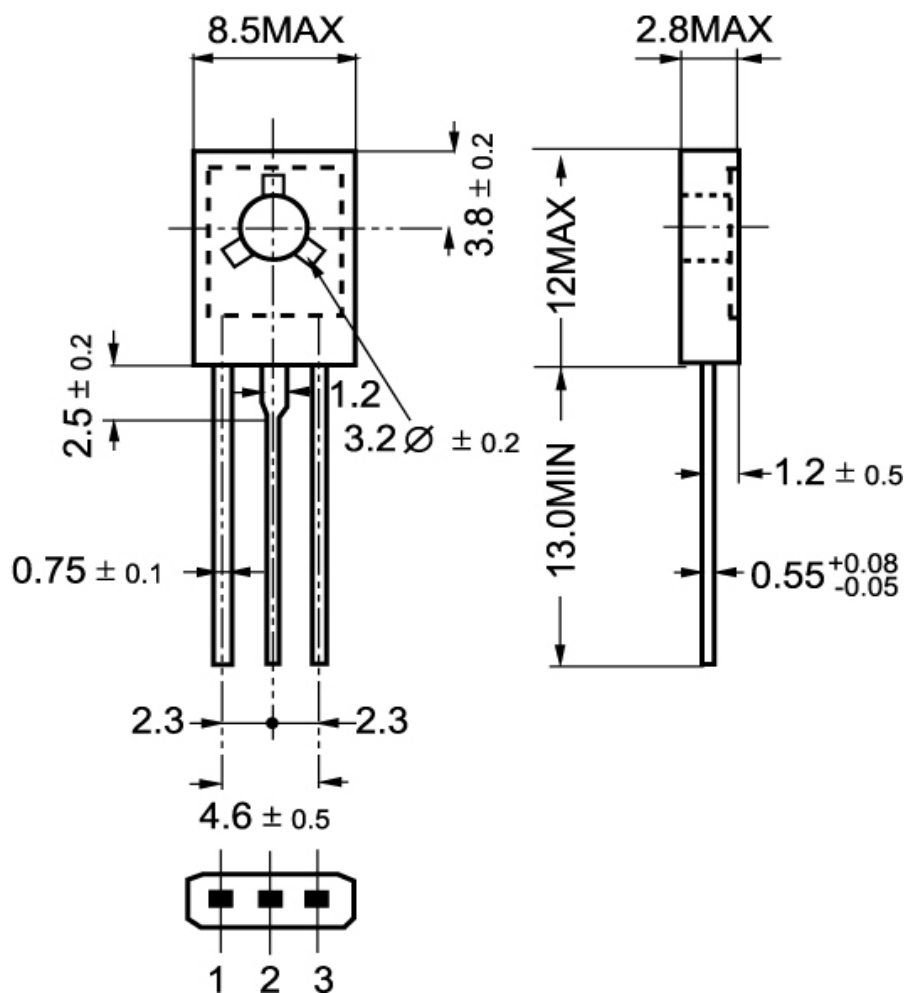


Fig.2 Outline dimensions